



CentralTM Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CLL4150 type is an ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in a hermetically sealed glass surface mount package, designed for high speed switching applications.

Marking Code: Cathode Band.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Continuous Reverse Voltage	V _R	50	V
Peak Repetitive Reverse Voltage	V _{RRM}	50	V
Continuous Forward Current	I _F	300	mA
Peak Repetitive Forward Current	I _{FRM}	600	mA
Forward Surge Current, tp=1 μsec.	I _{FSM}	4000	mA
Forward Surge Current, tp=1 sec.	I _{FSM}	1000	mA
Power Dissipation	P _D	500	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +200	°C
Thermal Resistance	θ _{JA}	350	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
BV _R	I _R =5.0μA	75		V
I _R	V _R =50V		100	nA
V _F	I _F =1.0mA	0.54	0.62	V
V _F	I _F =10mA	0.66	0.74	V
V _F	I _F =50mA	0.76	0.86	V
V _F	I _F =100mA	0.82	0.92	V
V _F	I _F =200mA	0.87	1.0	V
C _T	V _R =0, f=1 MHz		4.0	pF
t _{rr}	I _R =I _F =10mA, R _L =100Ω, Rec. to 1.0mA		4.0	ns

All dimensions in inches (mm).

